		
	Application No.	Applicant(s)
Notice of Allowability	10/604,406	HSU ET AL.
	Examin r	Art Unit
	Tu-Tu Ho	2818
The MAILING DATE of this communication app All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85 NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT F of the Office or upon petition by the applicant. See 37 CFR 1.31 1. This communication is responsive to Paper filed 18 July 2 2. The allowed claim(s) is/are 1-9. 3. The drawings filed on 18 July 2003 are accepted by the E 4. Acknowledgment is made of a claim for foreign priority un a) All b) Some* c) None of the: 1. Certified copies of the priority documents hav 2. Certified copies of the priority documents hav 3. Copies of the certified copies of the priority documents	tears on the cover sheet with the country of the co	plication. If not included n will be mailed in due course. THIS o withdrawal from issue at the initiative
International Bureau (PCT Rule 17.2(a)). * Certified copies not received: 5. Acknowledgment is made of a claim for domestic priority to (a) The translation of the foreign language provisional 6. Acknowledgment is made of a claim for domestic priority to Applicant has THREE MONTHS FROM THE "MAILING DATE" of below. Failure to timely comply will result in ABANDONMENT of	application has been received. under 35 U.S.C. §§ 120 and/or 121. of this communication to file a reply c	omplying with the requirements noted
7.		
 8. CORRECTED DRAWINGS must be submitted. (a) including changes required by the Notice of Draftspe 1) hereto or 2) to Paper No. (b) including changes required by the proposed drawing (c) including changes required by the attached Examine 	correction filed, which has b	een approved by the Examiner.
Identifying indicia such as the application number (see 37 CFR each sheet.	1.84(c)) should be written on the drawi	ngs in the front (not the back) of
9. DEPOSIT OF and/or INFORMATION about the depondance of the depondent of the depondent regarding REQUIREMENT FOR the depondent of the depondent regarding REQUIREMENT FOR the depondent of the	osit of BIOLOGICAL MATERIAL I THE DEPOSIT OF BIOLOGICAL MA	must be submitted. Note the TERIAL.
Attachment(s)	_	
 Notice of References Cited (PTO-892) Notice of Draftperson's Patent Drawing Review (PTO-948) Information Disclosure Statements (PTO-1449), Paper No Examiner's Comment Regarding Requirement for Deposit of Biological Material 	4☐ Interview Summ — 6☐ Examiner's Ame	al Patent Application (PTO-152) lary (PTO-413), Paper No endment/Comment ement of Reasons for Allowance
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DETAILED ACTION

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Allowable Subject Matter

1. Claims 1-9 are allowable over the prior art of record.

The following is an examiner's statement of reasons for allowance: The prior art of record fails to teach or render obvious a flash memory with all limitations as recited in claim 1. Specifically, the prior art of record, in disclosing flash memory systems with global and local bit lines, fails to disclose that the source of each memory cell consists of a first doped region of the first conductivity type and a second doped region of the second conductivity type that surrounds the first doped region and is short-circuited with the first doped region.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

- 2. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure. Copies of the references are not being furnished with this Office Action per MPEP § 707.05(a).
- a. U.S. Patent 6,038,170 to Shiba discloses a semiconductor integrated circuit device including a plurality of divided sub-bit lines wherein source and drain regions are formed in doped wells.

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b. U.S. Patent 6,172,397 to Oonakado et al. discloses a non-volatile semiconductor

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memory device having a p type source region and a p type drain region being formed in a surface

of an n well and having a data program means for injecting electrons from within the drain

region to the floating gate charge storage electrode by hot electron injection induced by a band-

to-band tunnel current.

3. Any inquiry concerning this communication or earlier communications from the

examiner should be directed to Tu-Tu Ho whose telephone number is (703) 305-0086. The

examiner can normally be reached on 6:30 am - 5:00 pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's

supervisor, DAVID NELMS can be reached on (703) 308-4910. The fax phone numbers for the

organization where this application or proceeding is assigned are (703) 872-9306 for regular

communications and (703) 872-9306 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding

should be directed to the receptionist whose telephone number is (703) 308-1782.

Tu-Tu Ho

October 23, 2003

✓ David Nelms Supervisory Patent Examinor

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